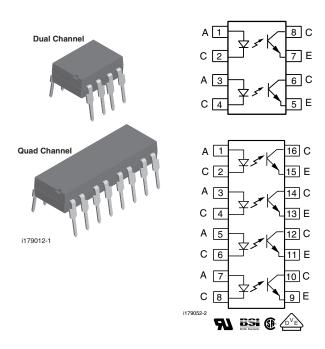
COMPLIANT



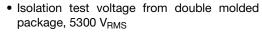
Vishay Semiconductors

Optocoupler, Phototransistor Output (Dual, Quad Channel)



FEATURES

- Identical channel to channel footprint
- Dual and quad packages feature:
 - Reduced board space
 - Lower pin and parts count
 - Better channel to channel CTR match
 - Improved common mode rejection



• Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

AGENCY APPROVALS

- UL1577, file no. E52744 system code H, double protection
- CSA 93751
- BSI IEC 60950; IEC 60065
- DIN EN 60747-5-2 (VDE0884)/DIN EN 60747-5-5 pending, available with option 1

DESCRIPTION

The ILD615, ILQ615 are multi-channel phototransistor optocouplers that use GaAs IRLED emitters and high gain NPN phototransistors. These devices are constructed using over/under leadframe optical coupling and double molded insulation technology resulting a withstand test voltage of 7500 VAC_{PEAK} and a working voltage of 1700 V_{RMS}.

The binned min./max. and linear CTR characteristics make these devices well suited for DC or AC voltage detection. Eliminating the phototransistor base connection provides added electrical noise immunity from the transients found in many industrial control environments.

Because of guaranteed maximum non-saturated and saturated switching characteristics, the ILD615, ILQ615 can be used in medium speed data I/O and control systems. The binned min./max. CTR specification allow easy worst case interface calculations for both level detection and switching applications. Interfacing with a CMOS logic is enhanced by the guaranteed CTR at $I_F = 1$ mA.

ILD615, ILQ615





ORDERING INFO	RMATION							
I L x 6 1 5 - # X 0 # # T								Option 6 10.16 mm Option 9 > 0.1 mm
AGENCY		DUAL C	HANNEL			QUAD C	HANNEL	
CERTIFIED/PACKAGE				CTR				
				10 :				
UL, CSA, BSI, VDE	40 to 80	63 to 125	100 to 200	160 to 320	40 to 80	63 to 125	100 to 200	160 to 320
DIP-8	ILD615-1	ILD615-2	ILD615-3	ILD615-4	-	ı	-	-
DIP-8, 400 mil, option 6	-	-	-	ILD615-4X006	-	-	-	-
SMD-8, option 7	ILD615-1X007T	-	-	-	-	-	-	-
SMD-8, option 9	ILD615-1X009	ILD615-2X009T ⁽¹⁾	ILD615-3X009T	ILD615-4X009T ⁽¹⁾	-	-	-	-
DIP-16	-	-	-	-	ILQ615-1	ILQ615-2	ILQ615-3	ILQ615-4
SMD-16, option 7	-	-	-	-	-	ILQ615-2X007	ILQ615-3X007T ⁽¹⁾	ILQ615-4X007
SMD-16, option 9	-	-	-	-	ILQ615-1X009	1	ILQ615-3X009T ⁽¹⁾	ILQ615-4X009T ⁽¹⁾
VDE	40 to 80	63 to 125	100 to 200	160 to 320	40 to 80	63 to 125	100 to 200	160 to 320
DIP-8	-	ILD615-2X001	-	ILD615-4X001	-	-	-	-
DIP-8, 400 mil, option 6	-	ILD615-2X016	ILD615-3X016	ILD615-4X016	-	-	=	=
SMD-8, option 7	-	-	ILD615-3X017T ⁽¹⁾	-	-	-	-	-
DIP-16	-	-	-	-	-	-	ILQ615-3X001	ILQ615-4X001
DIP-16, 400 mil, option 6	-	-	-	-	-	-	ILQ615-3X016	-
SMD-16, option 7	-	=	-	-	-	ILQ615-2X017	=	-

Notes

- Also available in tubes; do not add T to end.
- Additional options may be possible, please contact sales office.

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT				
INPUT								
Reverse voltage		V_R	6	V				
Forward current		I _F	60	mA				
Surge current		I _{FSM}	1.5	Α				
Power dissipation		P _{diss}	100	mW				
Derate linearly from 25 °C			1.33	mW/°C				
OUTPUT								
Collector emitter breakdown voltage		BV _{CEO}	70	V				
Emitter collector breakdown voltage		BV _{ECO}	7	V				
Callactor august		I _C	50	mA				
Collector current	t < 1 ms	I _C	100	mA				
Power dissipation		P _{diss}	150	mW				
Derate linearly from 25 °C			2	mW/°C				



ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT				
COUPLER								
Storage temperature		T _{stg}	- 55 to + 150	°C				
Operating temperature		T _{amb}	- 55 to + 100	°C				
Junction temperature		Tj	100	°C				
Soldering temperature (1)	2 mm distance from case bottom	T _{sld}	260	°C				
Package power dissipation ILD615			400	mW				
Derate linearly from 25 °C			5.33	mW/°C				
Package power dissipation ILQ615			500	mW				
Derate linearly from 25 °C			6.67	mW/°C				
Isolation test voltage	t = 1 s	V _{ISO}	5300	V _{RMS}				
Isolation voltage		V _{IORM}	890	V_P				
Total power dissipation		P _{tot}	250	mW				
Creepage distance			≥ 7	mm				
Clearance distance			≥ 7	mm				
Isolation resistance	V _{IO} = 500 V, T _{amb} = 25 °C	R _{IO}	400 5.33 r 500 6.67 r 5300 890 250 ≥ 7 ≥ 7 ≥ 10 ¹²	Ω				
isolation resistance	$V_{IO} = 500 \text{ V}, T_{amb} = 100 ^{\circ}\text{C}$	R _{IO}	≥ 10 ¹¹	Ω				

Notes

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not
 implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute
 maximum ratings for extended periods of the time can adversely affect reliability.
- (1) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

ELECTRICAL CHARACTERISTCS (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT								
Forward voltage	I _F = 10 mA	V _F	1	1.15	1.3	V		
Breakdown voltage	$I_R = 10 \mu A$	V_{BR}	6	30		V		
Reverse current	V _R = 6 V	I _R		0.01	10	μΑ		
Capacitance	$V_R = 0 V$, $f = 1 MHz$	Co		25		pF		
Thermal resistance, junction to lead		R _{THJL}		750		K/W		
OUTPUT								
Collector emitter capacitance	$V_{CE} = 5 \text{ V}, f = 1 \text{ MHz}$	C _{CE}		6.8		pF		
Collector emitter leakage current, -1, -2	$V_{CE} = 10 \text{ V}$	I _{CEO}		2	50	nA		
Collector emitter leakage current, -3, -4	V _{CE} = 10 V	I _{CEO}		5	100	nA		
Collector emitter breakdown voltage	$I_{CE} = 0.5 \text{ mA}$	BV _{CEO}	70			٧		
Emitter collector breakdown voltage	$I_E = 0.1 \text{ mA}$	BV _{ECO}	7			V		
Thermal resistance, junction to lead		R _{THJL}		500		K/W		
PACKAGE TRANSFER CHARACTERISTI	cs							
Channel/channel CTR match	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	CTRX/CTRY	1 to 1		2 to 1			
COUPLER								
Capacitance (input to output)	$V_{IO} = 0 V$, $f = 1 MHz$	C _{IO}		0.8		pF		
Insulation resistance	V _{IO} = 500 V, T _A = 25 °C	R _S	10 ¹²	10 ¹⁴		Ω		
Channel to channel isolation			500			VAC		

Note

Minimum and maximum values are tested requierements. Typical values are characteristics of the device and are the result of engineering
evaluations. Typical values are for information only and are not part of the testing requirements.

ILD615, ILQ615



Vishay Semiconductors Optocoupler, Phototransistor Output (Dual, Quad Channel)

CURRENT TRANSFER RATIO (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
		ILD615-1	CTR _{CEsat}		25	TYP. MAX. 25 40 60 100 30 45 70 90 60 80 80 125 150 200 200 320	%	
		ILQ615-1	CINCEsat		25		70	
		ILD615-2	CTD		40		%	
Current transfer ratio	I _F = 10 mA, V _{CE} = 0.4 V	ILQ615-2	CTR _{CEsat}		40		70	
(collector emitter saturated)	IF = 10 IIIA, VCE = 0.4 V	ILD615-3	CTD.		60		%	
		ILQ615-3	CTR _{CEsat}		00	80 125	70	
		ILD615-4	CTR _{CEsat} 10		100		%	
		ILQ615-4	CINCEsat		100	30	70	
		ILD615-1	CTR _{CF}	13	30		%	
	I _F = 1 mA, V _{CF} = 5 V	ILQ615-1	OTHCE	10	30		70	
		ILD615-2	CTR _{CE}	22	15		%	
		ILQ615-2			40		70	
	IF = 1 IIIA, VCE = 3 V	ILQ615-2 CTR _{CE} 22 45 ILD615-3 CTR _{CE} 34 70		%				
		ILQ615-3	Q615-2 CTR _{CE} 22 45 D615-3 Q615-3 CTR _{CE} 34 70	70				
		ILD615-4	CTR _{CF}	56	90		%	
Current transfer ratio		ILQ615-4	OTHCE	30	30		70	
(collector emitter)		ILD615-1	CTR _{CE}	40	60	80	%	
		ILQ615-1	OTHCE	40	00	00	70	
		ILD615-2	CTR _{CF}	63	80	125	%	
	$I_{E} = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	ILQ615-2	OTHCE	0	00	123	70	
	1- 10 11174, VCE = 5 V	ILD615-3	CTR _{CE}	100	150	200	%	
		ILQ615-3	OTTICE	100	130	200	/0	
		ILD615-4	CTR _{CE}	160	160 200	200	%	
		ILQ615-4	OTHCE	100	200	520	70	

SAFETY AND INSULATION RATED PARAMETERS									
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Partial discharge test voltage - routine test	100 %, t _{test} = 1 s	V _{pd}	1.669			kV			
Partial discharge test voltage -	$t_{Tr} = 60 \text{ s}, t_{test} = 10 \text{ s},$	V_{IOTM}	10			kV			
lot test (sample test)	(see figure 2)	V_{pd}	1.424			kV			
	V _{IO} = 500 V	R _{IO}	10 ¹²			Ω			
Insulation resistance	V _{IO} = 500 V, T _{amb} = 100 °C	R _{IO}	10 ¹¹			Ω			
insulation resistance	V _{IO} = 500 V, T _{amb} = 175 °C (construction test only)	R _{IO}	10 ⁹			Ω			
Forward current		I _{SI}			275	mA			
Power dissipation		P _{SO}			400	mW			
Rated impulse voltage		V _{IOTM}			10	kV			
Safety temperature		T _{SI}			175	°C			

Note

• According to DIN EN 60747-5-2 (see figure 2). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.



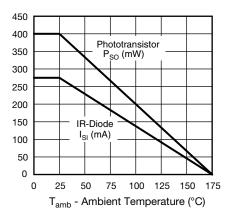


Fig. 1 - Derating Diagram

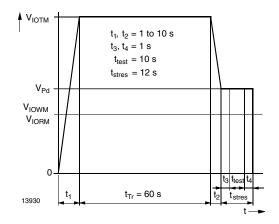


Fig. 2 - Test Pulse Diagram for Sample Test according to DIN EN 60747-5-2 (VDE0884); IEC60747-5-5

SWITCHING CHARACT	ERISTICS (T _{amb} = 25 °C, unless of	otherwise	specified)				
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
NON-SATURATED							
Current	$V_{CC} = 5 \text{ V}, R_L = 75 \Omega, 50 \% \text{ of } V_{PP}$		I _F		10		mA
Turn-on time	$V_{CC} = 5 \text{ V}, R_L = 75 \Omega, 50 \% \text{ of } V_{PP}$		t _{on}		3		μs
Rise time	V_{CC} = 5 V, R_L = 75 Ω , 50 % of V_{PP}		t _r		2		μs
Turn-off time	$V_{CC} = 5 \text{ V}, R_L = 75 \Omega, 50 \% \text{ of } V_{PP}$		t _{off}		2.3		μs
Fall time	$V_{CC} = 5 \text{ V}, R_L = 75 \Omega, 50 \% \text{ of } V_{PP}$		t _f		2		μs
Propagation H to L	V_{CC} = 5 V, R_L = 75 Ω , 50 % of V_{PP}		t _{PHL}		1.1		μs
Propagation L to H	V_{CC} = 5 V, R_L = 75 Ω , 50 % of V_{PP}		t _{PLH}		2.5		μs
SATURATED							
		ILD615-1			20	MAX.	A
		ILQ615-1	- I _F		20		mA
		ILD615-2			10		mA
Comment	$V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega,$	ILQ615-2	I _F		10		MA
Current	V _{TH} = 1.5 V	ILD615-3			10		A
		ILQ615-3	- I _F		10		mA
		ILD615-4			5		A
		ILQ615-4	- I _F		5		mA
		ILD615-1	_		3		
		ILQ615-1	t _{on}		3		μs
		ILD615-2			4.0		
Town on the c	$V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega,$	ILQ615-2	t _{on}		4.3		μs
Turn-on time	V _{TH} = 1.5 V	ILD615-3	_		4.3		
		ILQ615-3	- t _{on}		4.3		μs
		ILD615-4			6		
		ILQ615-4	- t _{on}		0		μs

ILD615, ILQ615



Vishay Semiconductors Optocoupler, Phototransistor Output (Dual, Quad Channel)

SWITCHING CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
SATURATED					•	•	•	
		ILD615-1						
		ILQ1615-1	- t _r		2		μs	
		ILD615-2			N. TYP. MAX. 2 2.8 2.8 4.6 18 25 25 25 11 14 14 15 1.6 2.6 2.6 5.4 8.6 7.2 7.4	_		
Diag times	$V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega,$	ILQ615-2	- t _r		2.8	MAX.	μs	
Rise time	V _{TH} = 1.5 V	ILD615-3			0.0			
		ILQ615-3	- t _r		2.8		μs	
		ILD615-4			4.6	2 2.8 2.8 4.6 18 25 25 25 11 14 14 15 1.6 2.6 2.6 5.4 8.6 7.2 7.2		
		ILQ615-4	- t _r		2 2.8 2.8 4.6 18 25 25 25 11 14 14 15 1.6 2.6 2.6 5.4 8.6 7.2	μs		
		ILD615-1			40		_	
		ILQ615-1	t _{off}		18		μs	
		ILD615-2			0.5		_	
T	$V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega,$	ILQ615-2	t _{off}		25	MAX.	μs	
Turn-off time	V _{TH} = 1.5 V	ILD615-3						
		ILQ615-3	- t _{off}		25		μs	
		ILD615-4						
		ILQ615-4	t _{off}		25		μs	
		ILD615-1						
		ILQ615-1	t _f		11		μs	
		ILD615-2						
	$V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega,$	ILQ615-2	t _f		2 2.8 2.8 4.6 18 25 25 25 11 14 14 15 1.6 2.6 2.6 5.4 8.6 7.2 7.2	μs		
Fall time	V _{TH} = 1.5 V	ILD615-3						
		ILQ615-3	t _f			μs		
		ILD615-4						
		ILQ615-4	- t _f			μs		
		ILD615-1						
		ILQ615-1	t _{PHL}		1.6		μs	
		ILD615-2						
	$V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega,$	ILQ615-2	t _{PHL}		2.6		μs	
Propagation H to L	V _{TH} = 1.5 V	ILD615-3						
		ILQ615-3	t _{PHL}		2.6		μs	
		ILD615-4						
		ILQ615-4	t _{PHL}		5.4		μs	
		ILD615-1						
		ILQ615-1	t _{PLH}		8.6	1	μs	
		ILD615-2			 	 	<u> </u>	
	$V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega,$	ILQ615-2	t _{PLH}		7.2		μs	
Propagation L to H	$V_{TH} = 1.5 \text{ V}$	ILD615-3						
		ILQ615-3	t _{PLH}		4.6 18 25 25 25 11 14 14 15 1.6 2.6 2.6 5.4 8.6 7.2 7.2	μs		
		ILD615-4			 	MAX.	 	
		ILQ615-4	t _{PLH}		7.4		μs	

COMMON MODE TRANSIENT IMMUNITY (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Common mode rejection output high	$V_{CM} = 50 \ V_{P-P}, \ R_L = 1 \ k\Omega, \ I_F = 0 \ mA$	CM _H		5000		V/µs		
Common mode rejection output low	$V_{CM} = 50~V_{P-P},~R_L = 1~k\Omega,~I_F = 0~mA$	CML		5000		V/µs		
Common mode coupling capacitance		C _{CM}		0.01		pF		



TYPICAL CHARACTERISTICS ($T_{amb} = 25$ °C, unless otherwise specified)

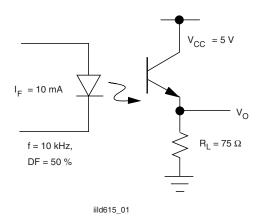


Fig. 3 - Non-Saturated Switching Timing

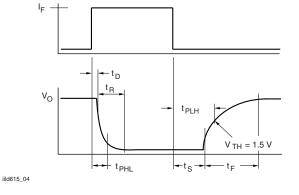


Fig. 6 - Saturated Switching Timing

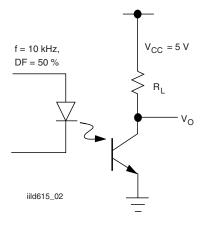


Fig. 4 - Saturated Switching Timing

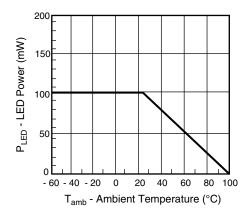


Fig. 7 - Maximum LED Power Dissipation

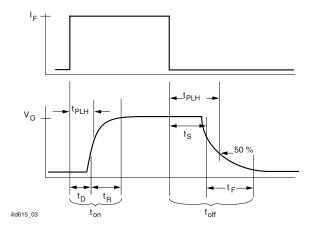


Fig. 5 - Non-Saturated Switching Timing

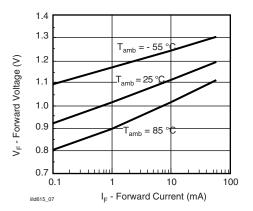


Fig. 8 - Forward Voltage vs. Forward Current

Vishay Semiconductors Optocoupler, Phototransistor Output (Dual, Quad Channel)



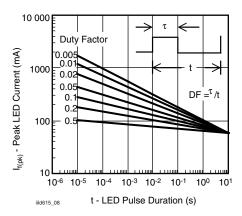


Fig. 9 - Peak LED Current vs. Pulse Duration, $\boldsymbol{\tau}$

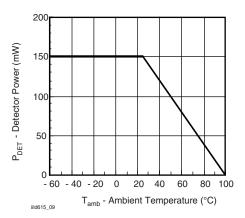


Fig. 10 - Maximum Detector Power Dissipation

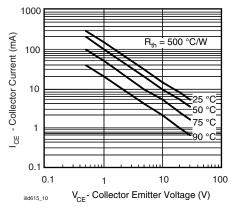


Fig. 11 - Maximum Collector Current vs. Collector Voltage

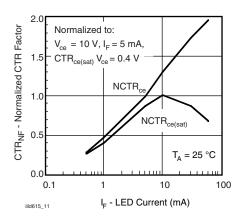


Fig. 12 - Normalization Factor for Non-Saturated and Saturated CTR vs. I_{F}

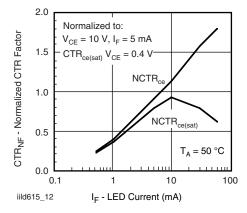


Fig. 13 - Normalization Factor for Non-Saturated and Saturated CTR vs. I_{F}

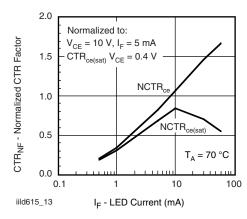


Fig. 14 - Normalization Factor for Non-Saturated and Saturated CTR vs. I_{F}



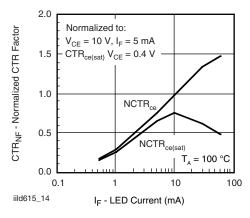


Fig. 15 - Normalization Factor for Non-Saturated and Saturated CTR vs. I_{F}

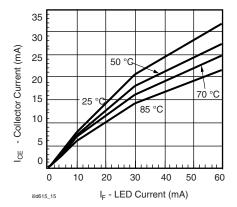


Fig. 16 - Collector Emitter Current vs. Temperature and LED Current

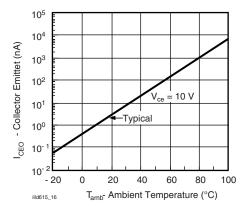


Fig. 17 - Collector Emitter Leakage vs. Temperature

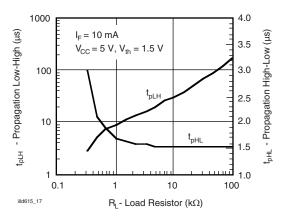


Fig. 18 - -1, Propagation Delay vs. Collector Load Resistor

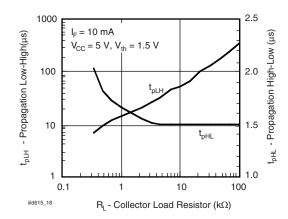


Fig. 19 - -2, -3, Propagation Delay vs. Collector Load Resistor

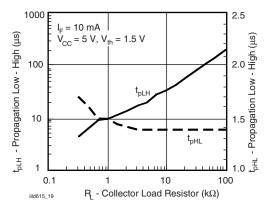
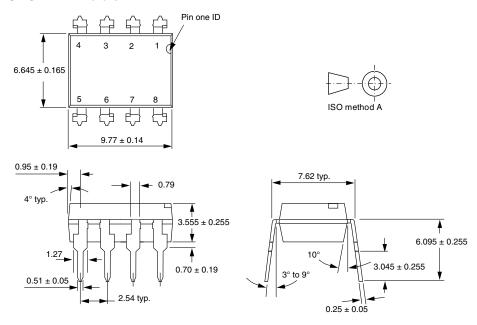


Fig. 20 - -4, Propagation Delay vs. Collector Load Resistor

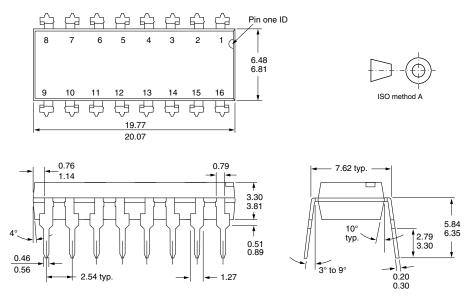
Vishay Semiconductors Optocoupler, Phototransistor Output (Dual, Quad Channel)



PACKAGE DIMENSIONS in millimeters

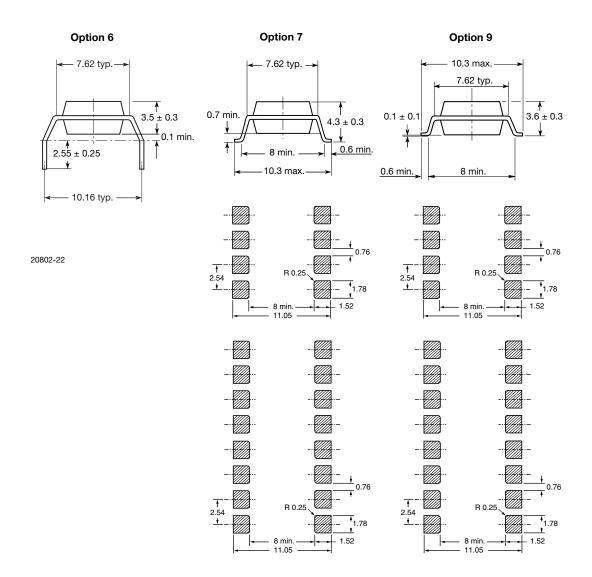


i178006



i178007





PACKAGE MARKING



Notes

- Only options 1 and 7 reflected in the package marking.
- The VDE Logo is only marked on option1 parts.
- Tape and reel suffix (T) is not part of the package marking.



Legal Disclaimer Notice

Vishay

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